



# Compact PMIC with Source Voltage Level Configuration for Single/ Dual PV Cells or Pulsed Source

### **Features and Benefits**

Cold start from 250 mV input voltage and 5  $\mu$ W input power (typical)

- Fast start-up from source.

Constant input voltage regulation (0.12 V to 1.47 V)

 Optimized for single/dual elements capacitive PV cell, intermittent and pulsed power sources.

Selectable overdischarge and overcharge protection

- Supports various types of rechargeable batteries (LiC, Li-ion, LiPo, Li-ceramic pouch, etc.).

Ultra-low power idle mode

- Stored energy is preserved when no source available.

#### Shipping and shelf mode

- Prevents energy drain from battery when no source available (KEEP\_ALIVE pin);
- Disables storage element charging (DIS STO CH pin).

#### Configuration pins or I<sup>2</sup>C

- Easy setup;
- Basic settings at start-up with configuration pins;
- Advanced configuration with I<sup>2</sup>C (Fast Mode Plus).

#### Average power monitoring

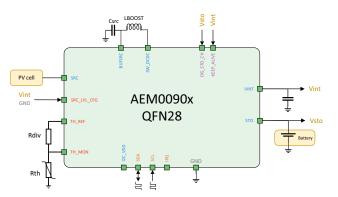
- Easy estimation of the charging power.

#### Integrated thermistor conditioning circuit

- Configurable battery thermal protection.

# **Applications**

Wearable Electronics	Keyboards
Remote Control	Electronic Shelf Labels
Smart Buildings	Indoor Sensors



# Description

The AEM0090x is a compact, fully integrated battery charger that harvests DC power to store energy in rechargeable batteries. It extends battery lifetime and removes the need for primary energy storage in a large range of applications.

Selecting the operating voltage allows the user to set a constant Maximum Power Point at which the AEM0090x operates, to charge a storage element, such as a Li-ion battery or a LiC. The boost converter operates with input voltages ranging from 120 mV to 1.47 V, making AEM0090x ideal for single or dual element PV cell.

The AEM0090x has a unique cold-start circuit capable of operation with input voltages as low as 250 mV and power as minimal as 5  $\mu W$ . The output voltages ranges from 2.8 V to 4.8 V, with configurable protection levels to prevent overcharging and overdischarging of the storage element. No external components are necessary to set these protection levels. Additionally, thermal monitoring safeguards the storage element, while an Average Power Monitoring system offers insights into the energy transfered to the storage element.

Thanks to the keep-alive feature, the AEM0090x internal circuit can stay powered by the storage element even in absence of a harvesting source. When keep-alive is disabled and no harvesting source is present, the AEM0090x turns off, preserving the energy of the storage element.

A shelf-mode can be obtained by disabling the keep-alive feature, preventing the battery to be drained during device storage. Furthermore, enabling the DIS\_STO\_CH feature creates a shipping mode by preventing battery charging.

The AEM00900 application schematic is featuring small PCB size (51 mm²) and a global lower bill of material. The AEM00901 application schematic allows higher performance with a PCB area penalty as low as 6 mm², enabling small size and low cost implementation for single/dual element PV or pulsed sources versus other DCDC based solutions.

### **Device Information**

Part Number	Package	Body size
10AEM00900C0000 10AEM00901C0000	QFN 28-pin	4x4mm

#### **Evaluation Board**

Part number	
2AAEM00900C001	
2AAEM00901C001	





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Figure 1: Simplified schematic view

#### 1. Introduction

The AEM0090x is a full-featured energy efficient battery charger able to charge a storage element (connected to STO) from an energy source (connected to SRC).

The core of the AEM0090x is a regulated switching converter (boost) with high-power conversion efficiency.

At first start-up, as soon as a required cold-start voltage of 250 mV and a sparse amount of power of at least 5  $\mu$ W is available at the source ( $V_{STO} > V_{OVDIS}$ ), the AEM0090x coldstarts. After the cold start, the AEM extracts the power available from the source if the input voltage is higher than

#### V<sub>SRC.REG</sub>.

The AEM0090x can be fully configured through I<sup>2</sup>C or partially by configuration pins. I<sup>2</sup>C configuration is not mandatory, as the default configuration is made to fit the most common needs, along with the configuration pins for the most common settings.

Through I<sup>2</sup>C communication or through the configuration pins, the user can select a specific operating mode from a variety of modes that cover most application requirements without any dedicated external component. The battery protection thresholds (V<sub>OVCH</sub> and V<sub>OVDIS</sub>) can be configured with the help of the STO\_CFG[2:0] pins. They can also be configured in 60 mV steps using the I<sup>2</sup>C bus.

Depending on the harvester, the source regulation voltage,  $V_{SRC,REG}$ , can be configured using six configuration pins (SRC\_LVL\_CFG[5:0]) or using I<sup>2</sup>C communication.

The AEM0090x features an optional temperature protection. It can be set through the  $I^2C$  interface and allows to define a temperature range so that, when the ambient temperature is outside that range, battery charging is disabled. One additional resistor and one additional thermistor are needed for this feature.

The KEEP\_ALIVE functionality sets the source from which the AEM0090x supplies its internal circuitry VINT. It can be supplied either from the harvester connected on SRC or from the battery connected to STO.

When KEEP\_ALIVE is disabled, the AEM0090x internal circuitry is running as long as enough energy is available on SRC. If no energy is available on SRC, the internal voltage drops down to reset voltage and the AEM needs to go through a cold start before being able to charge the battery again. This is useful for applications with long periods without energy on SRC and when the I<sup>2</sup>C is not used. If the I<sup>2</sup>C communication is used, the AEM will need to be reconfigured after the cold-start. With this setting, only a dozen nA of quiescent current is taken from the storage element.

When KEEP\_ALIVE is enabled, the AEM0090x is supplied by STO, the circuit stays in SUPPLY STATE or SLEEP STATE as long as the battery connected to STO is above the overdischarge threshold. It prevents losing the I<sup>2</sup>C configuration when energy harvesting is not occurring and offers faster reactivity as the AEM is not reset depending on the available energy on SRC.



# 2. Pin Configuration and Functions

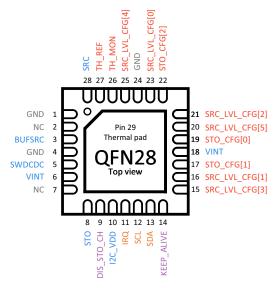


Figure 2: Pinout diagram QFN28

NAME	PIN NUMBER	Function			
Power Pins					
SRC	28	Connection to the harvested energy source.			
BUFSRC	3	Connection to an external capacitor buffering the boost converter input.			
SWDCDC	5	Switching node of the boost converter.			
VINT	6, 18	Internal supply voltage.			
STO	8	Connection to the energy storage element (rechargeable only). Cannot be left floating, voltage must always be above 2.5 V.			
I2C_VDD	10	Connection to supply the I <sup>2</sup> C interface.  - Connect to a 1.5 V to 5.0 V power supply if I <sup>2</sup> C is used.  - Connect to GND if I <sup>2</sup> C is not used.			
Configuration Pins					
STO_CFG[0]	19	Used for the configuration of the threshold voltages for the energy storage			
STO_CFG[1]	17	element.			
STO_CFG[2]	22	Read as HIGH if left floating.			
SRC_LVL_CFG[0]	23				
SRC_LVL_CFG[1]	16				
SRC_LVL_CFG[2]	21	Used for the configuration of the source voltage level.			
SRC_LVL_CFG[3]	15	Read as HIGH if left floating.			
SRC_LVL_CFG[4]	25				
SRC_LVL_CFG[5]	20				
TH_REF	27	Reference voltage for thermal monitoring. Leave floating if not used.			
TH_MON	26	Pin for temperature monitoring. Connect to VINT if not used.			
Control Pins					
DIS_STO_CH	9	When HIGH, the AEM stops charging the battery. Read as LOW if left floating.			
KEEP_ALIVE	14	When HIGH, the internal circuitry is supplied from STO. When LOW, the internal circuitry is supplied from SRC. Read as HIGH if left floating.			

Table 1: Pins description QFN28



### **DATASHEET**

NAME	PIN NUMBER	Function
I <sup>2</sup> C Pins		
SDA	13	Bidirectional data line.
JUA	13	Connect to I2C_VDD if not used.
SCL	12	Unidirectional serial clock for I <sup>2</sup> C.
301		Connect to I2C_VDD if not used.
IRQ	11	Output Interrupt request.
inq	11	Leave floating if not used.
Other pins		
GND	1, 4, 24, 29	Ground connection, each terminal should be strongly tied to the PCB ground
GIVD	(thermal pad)	plane, pin 29 (thermal pad) being the main GND connection of the AEM0090x.
NC	2, 7	Not connected pins, leave floating.

Table 1: Pins description QFN28





# 3. Specifications

# 3.1. Absolute Maximum Ratings

Parameter	Value
Voltage on SRC	2.0 V
Voltage on SWDCDC, STO, I2C_VDD, SDA, SCL, IRQ, DIS_STO_CH	5.5 V
Voltage on VINT, KEEP_ALIVE STO_CFG[2:0], SRC_LVL_CFG[5:0], TH_REF, TH_MON	2.75 V
Operating junction temperature	-40°C to 125°C

Table 2: Absolute maximum ratings

#### **ESD CAUTION**



ESD (ELECTROSTATIC DISCHARGE) SENSITIVE DEVICE

These devices have limited built-in ESD protection and damage may thus occur on devices subjected to high-energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality





# 3.2. Electrical Characteristics at 25 °C

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Power Conv	ersion					
D	Minimum source power required	During cold start AEM00900		2.47		μW
P <sub>SRC,CS</sub>	for cold start <sup>1</sup>	During cold start AEM00901		3.99		μW
V <sub>SRC,CS</sub>	Minimum source voltage required f	or cold start		0.25		V
V <sub>SRC,REG</sub>	Target regulation voltage of the sou SRC_LVL_CFG[5:0] configuration or		0.12		1.47	V
V <sub>OC</sub>	Open-circuit voltage of the source				2.0	V
Storage Eler	ment					
V <sub>STO</sub>	Voltage on the storage element		2.5		4.8	V
V <sub>OVCH</sub>	Maximum voltage accepted on the disabling its charging	storage element before	3	See	4.8	V
V <sub>OVDIS</sub>	Minimum voltage accepted on the storage element before stopping to supply VINT if Keep-alive is enabled.		2.8	section 6.3	4.05	V
Internal sup	ply & Quiescent Current		•			
V <sub>INT</sub>	Internal supply voltage	Auto-regulated, outside of reset and coldstart conditions.		2.2		V
I <sub>QSUPPLY</sub>	Quiescent current on STO in SUPPLY STATE	V <sub>STO</sub> = 3.7 V		242		nA
I <sub>QSLEEP</sub>	Quiescent current on STO in SLEEP STATE	V <sub>STO</sub> = 3.7 V		162		nA
I <sub>QSTO</sub>	Quiescent current on STO when Kee	ep-alive functionality is disabled		7.4		nA
I <sup>2</sup> C interface	•		·	·	·	
Bus frequency				400	1000	kHz
V <sub>I2C_VDD</sub>	I <sup>2</sup> C interface supply pin voltage		1.5		5.0	V
SCL SDA	- I <sup>2</sup> C interface communication pins		Pull-up to I2C_VDD with resistors			

Table 3: Electrical characteristics

<sup>1.</sup> These values are valid with the recommended BOM components (see Section 13)



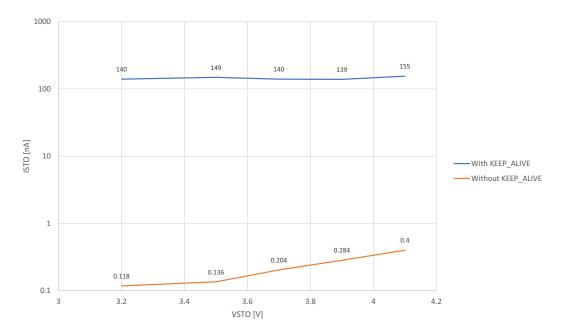


Figure 3: Quiescent current





# 3.3. Typical Characteristics

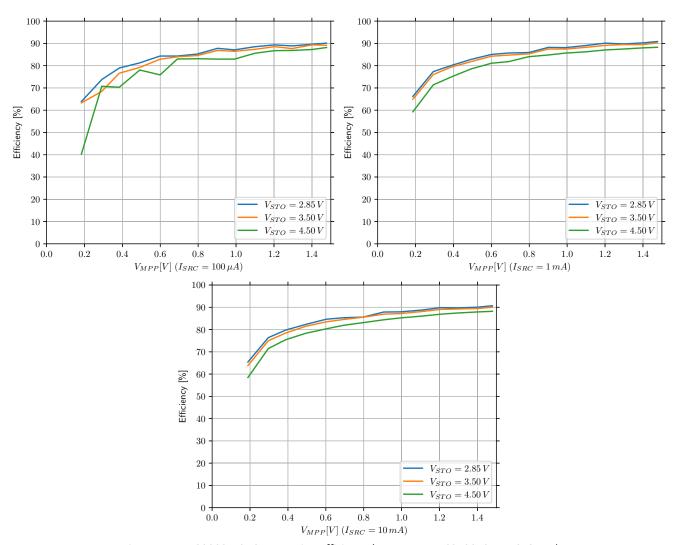


Figure 4: AEM00900 DCDC conversion efficiency (L<sub>DCDC</sub>: TDK VLS252012HBX-6R8M-1)

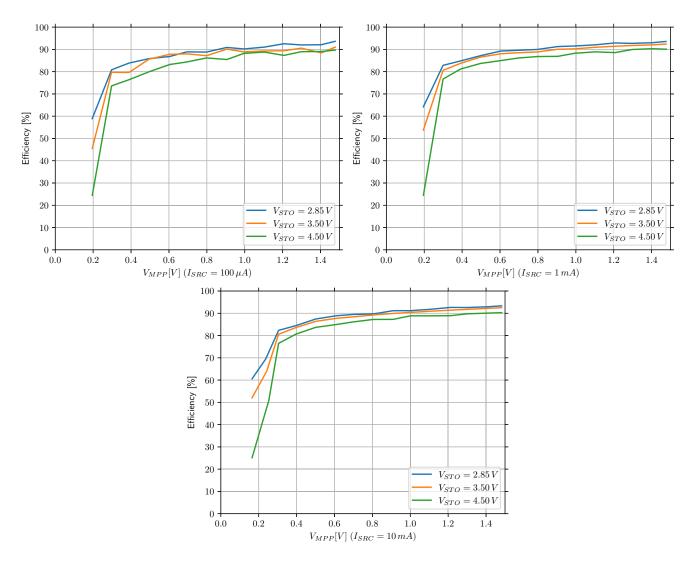


Figure 5: AEM00901 DCDC conversion efficiency (L<sub>DCDC</sub>: Coilcraft LPS4018-333MRB)





# 3.4. Recommended Operation Conditions

Symbol	Parameter		Min	Тур	Max	Unit
External Componen	ts					
1	Inductor of the boost converter	AEM00900	3.3	6.8		
LDCDC	inductor of the boost converter	AEM00901	6.8	33	47	μH
C <sub>SRC</sub>	Capacitor decoupling the BUFSRC terminal		10			μF
C <sub>INT</sub>	Capacitor decoupling V <sub>INT</sub>		3.3			μF
C <sub>STO</sub>	Capacitor decoupling the STO terminal <sup>1</sup>		5	22		μF
R <sub>DIV</sub>	Optional - pull-up resistor for the thermal monito	ring	5k	22k	33k	Ω
D	Optional - NTC thermistor for the thermal	R0		10k		Ω
R <sub>TH</sub>	monitoring	Beta		3380		К
R <sub>SCL</sub>	Optional - pull-up resistors for the I <sup>2</sup> C interface			1k		Ω
R <sub>SDA</sub>	Optional - pull-up resistors for the r C interface			IK		\$2
Logic input Pins						
SRC_LVL_CFG[5:0]	Logic HIGH		Connect to VINT			
SKC_LVL_CFG[5.0]	Configuration pins for the SRC voltage level	Logic LOW	Connect to GND			
STO_CFG[2:0]	Configuration pins for the storage element LC		Connect	Connect to VINT		
310_CFG[2.0]	thresholds	Logic LOW	Connect to GND			
KEEP ALIVE	Configuration for the "keep-alive" functionality	Logic HIGH	Connect to VINT			
KEEP_ALIVE	Configuration for the "keep-alive" functionality	Logic LOW	Connect to GND			
DIS STO CH	Configuration for disabling the charging of the	Logic HIGH	Connect	to STO		
DIS_STO_CH	battery	Logic LOW	Connect to GND			

Table 4: Recommended operating conditions

<sup>1.</sup> Decoupling capacitor of at least  $5\mu$ F is required to avoid damaging the AEM. The decoupling capacitor is to be sized according to the storage element internal resistance (ESR) to ensure optimal efficiency of the DCDC converter. It is recommended to use a capacitor of at least  $22 \mu$ F when measuring the AEM0090x efficiency with laboratory equipment such as source measurement units (SMU). A battery must be connected to STO when a harvester is connected to the AEM to avoid damaging it.



# 4. Functional Block Diagram

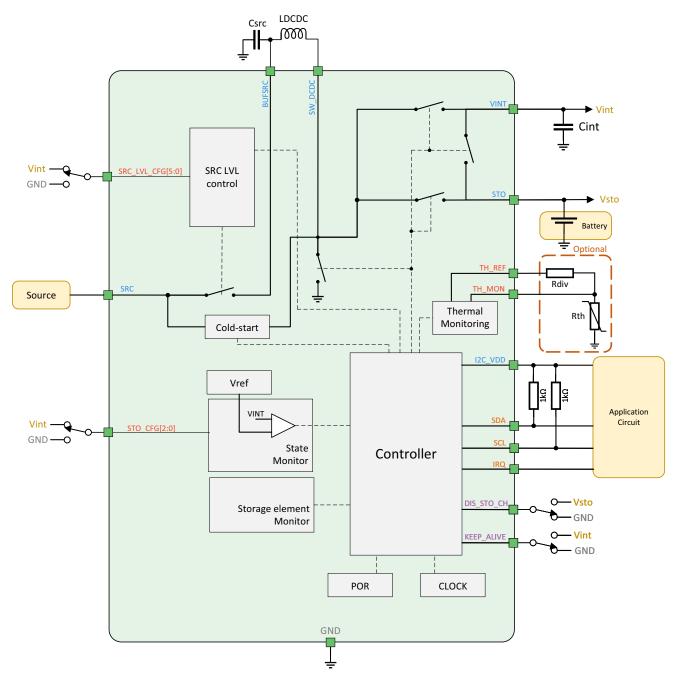


Figure 6: Functional block diagram



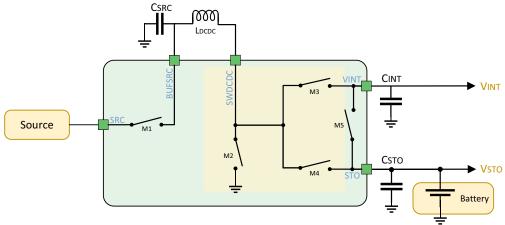


Figure 7: Simplified schematic view of the AEM0090x

## 5. Theory of Operation

#### 5.1. Boost Converter

The boost (step-up) converter raises the voltage available at BUFSRC to a level suitable for charging the storage element, in the range of 2.8 V to 4.8 V, according to the system configuration. The switching transistors of the boost converter are M2, M3 and M4. The reactive power component of this converter is the external inductor LDCDC.

When the boost converter is extracting energy from SRC, M1 is closed. BUFSRC is decoupled by the capacitor  $C_{SRC}$ , which smoothens the voltage against the current pulses induced by the boost converter.

The storage element is connected to the STO pin, whose voltage is V<sub>STO</sub>. This node is linked to the output of one of the high-side transistors (M4) of the boost converter. When energy harvesting is occurring, the boost converter charges the battery. If VINT drops below its regulation value and if the Keep-alive functionality is disabled, the AEM uses M3 instead of M4 as the high-side transistor of the boost converter until VINT reaches its target plus a small hysteresis. If the Keep-alive functionality is enabled, VINT is instead supplied from STO by modulating the gate of M5. In that case M3 is never used.

### 5.2. Source Voltage Regulation

During SUPPLY STATE, the voltage on SRC is regulated to a voltage configured by the user. The AEM0090x offers a large choice of values for the source voltage. If the open-circuit voltage of the harvester is lower than  $V_{SRC,REG}$ , the AEM0090x does not extract the power from the source. If the SRC voltage is higher, the AEM0090x regulates  $V_{SRC,REG}$  and extracts power.

### 5.3. Thermal Monitoring

Thermal monitoring allows to protect the storage element by disabling the charge of the storage element and setting the STATUS.TEMP register when the temperature is outside of the defined temperature range. Enabling this functionality requires the use of a resistor (R<sub>DIV</sub>) and a thermistor (R<sub>TH</sub>). See Figure 8 for external components connections. The TH\_REF terminal allows a reference voltage to be applied to the resistive divider while TH\_MON is the measuring point. An ADC is measuring the voltage on TH\_MON between 0 and 1 V. The temperature evaluation is done periodically (T<sub>TEMP,MON</sub>) to spare power. Information for the thermal monitoring is described in Section 9.4. Thermal monitoring is optional, if not used connect TH\_MON to VINT and leave TH\_REF floating.

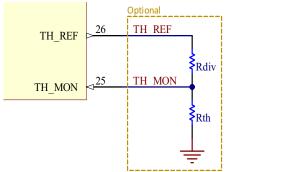


Figure 8: TH\_REF and TH\_MON connections

# 5.4. Average Power Monitoring

The Average Power Monitoring (APM) allows to evaluate the energy transfer from SRC to STO.



# AEM00900 AEM00901

# 5.5. Automatic High-power Mode (AEM00900 only)

When the AEM detects that the energy available on SRC is high enough, the boost converter automatically switches to high-power mode, increasing the harvesting current capability at the price of a slight efficiency degradation.

Preventing the AEM to switch to high-power mode may allow to use an inductor with half peak current rating for  $L_{DCDC}$  (see Section 6.5.2). On the other hand, allowing the AEM to switch to high-power mode increases the maximum current that the AEM can harvest from SRC to STO.

Automatic high-power mode is enabled by default and can be disabled by setting the PWR.HPEN to 0 through the  $I^2C$  interface.

NOTE: this feature is not available on the AEM010901, that is always in high-power mode.

## 5.6. Keep-alive

The internal circuitry connected to VINT can be supplied either by SRC through the boost converter (keep-alive disabled), or by the battery STO (keep-alive enabled).

When the keep-alive feature is disabled, the AEM0090x is supplied from SRC. The AEM will switch to RESET STATE if the energy on SRC is not sufficient.

When the keep-alive feature is enabled, the AEM0090x is supplied from STO. VINT is regulated as long as  $V_{STO} > V_{OVDIS}$ . The keep-alive feature allows to maintain the  $I^2C$  registers configuration and therefore preventing the loss of volatile memory. Referring to Table 3, the quiescent current is then  $I_{QSUPPLY}$  or  $I_{QSLEEP}$ , depending on whether the AEM0090x is in SUPPLY STATE or in SLEEP STATE.

#### **5.7. IRQ Pin**

The IRQ pin allows user to get notified when various events happen (rising edge on IRQ pin). At start-up, the only flag that is enabled is I2CRDY, allowing user to know when the AEM0090x has finished to coldstart and thus, is out of RESET STATE and is ready to be programmed through I<sup>2</sup>C. Other flags can be enabled by writing the IRQEN register (Section 9.9). When the IRQ pin shows a rising edge, the flags can be determined by reading the IRQFLG register (Section 9.11). Reading the registers will reset the IRQ pin and clear the IRQFLG register.

### 5.8. State Description

Unless stated otherwise, all values given in this section are typical.

#### 5.8.1. Reset State

In RESET STATE all nodes are deeply discharged and there is no available energy to be harvested. The AEM stays in this state until the source connected to SRC meets the cold start requirements long enough to make VINT rise up to 2.3 V. Cold start requirements depend on the AEM version and the  $L_{DCDC}$  inductor (see Figure 4 and Figure 5).

When VINT has reached 2.3 V, the AEM0090x reads the configuration pins and switches to SENSE STO STATE.

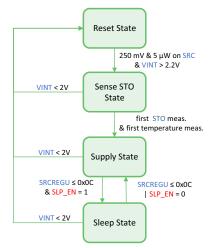


Figure 9: Diagram of the AEM0090x state machine

#### 5.8.2. Sense STO State

In SENSE STO STATE the AEM0090x does the following measurements in order to know if the charging condition of the battery are met:

- Battery voltage on STO;
- Temperature through pins TH\_MON and TH\_REF (see Section 5.3. and 9.4.).

In this state, Once the measurements are done, AEM0090x switches to SUPPLY STATE.

#### 5.8.3. Supply State

In SUPPLY STATE, the AEM transfers charges directly from to STO while maintaining  $V_{\rm INT}$ .

If  $V_{INT}$  drops and the energy available on SRC is not sufficient to make  $V_{INT}$  rise again, there are two possible behaviors, depending on the 'keep-alive' feature:

- If keep-alive is enabled, VINT is supplied by the battery through M5, so the AEM0090x stays in SUPPLY STATE while energy is available on the battery;
- If keep-alive is disabled, VINT will no longer be maintained and the AEM switches to RESET STATE.





### 5.8.4. Sleep State

Please note that the first condition for the AEM0090x to enter SLEEP STATE is to set the SLEEP.EN field in the SLEEP register 1, as shown on Figure 9.

In SLEEP STATE, the AEM power consumption is reduced. This mode may be used when the power available on the input is presumably low.

The AEM0090x enters sleep mode when the following conditions are met:

- Field SLEEP.EN in the SLEEP register is set to 1 and SRCREGU.VALUE register value is set below SLEEP.SRCTHRESH (I<sup>2</sup>C).
- Temperature is out of range.
- V<sub>STO</sub> ≥ V<sub>OVCH</sub>.
- DIS\_STO\_CH is HIGH.





# 6. System Configuration

### 6.1. Configuration Pins and I<sup>2</sup>C

#### 6.1.1. Configuration Pins

After a cold start, the AEM0090x reads the configuration GPIOs. Those are then read periodically every 2 s, with the exception of the DIS\_STO\_CH pin that is read every 1 s. The configuration pins can be changed on-the-fly and the corresponding configuration will be updated at the next IO reading. The floating configuration pins are read as HIGH, except DIS STO CH which is read as LOW.

#### 6.1.2. Configuration by I2C

To configure the AEM0090x through the I<sup>2</sup>C interface after a cold start, the user must wait for the IRQ pin to rise, showing that the AEM0090x is out of RESET STATE and is ready to communicate with I<sup>2</sup>C. The interrupt is reset by reading its register. Please note that the IRQ pin is always low during RESET STATE. See Section 9.11 for further informations about the IRQ pin.

Once IRQ goes HIGH, the user can then write to the desired registers and validate the configuration by setting the CTRL.UPDATE register field. All configuration pins are then ignored (with the exception of DIS\_STO\_CH, see Section 9.5) and all the configurations are set by the register values. All registers have a default value, that can be found in Table 7. It is possible to go back to the GPIO configuration by resetting the CTRL.UPDATE bit. To apply any modification to the configuration, simply change the wanted registers value and set the CTRL.UPDATE bit again.

Registers are stored in a volatile memory, so their value are lost when VINT drops below the reset voltage (2 V), making the AEM0090x switch to RESET STATE. Thus, when using the I<sup>2</sup>C configuration, it is highly recommended to enable the keep-alive (see section 9.5.). If keep-alive functionality is disabled, register configuration is lost every time the energy available on SRC is not sufficient to maintain V<sub>INT</sub> above the reset voltage (2 V typical).





# AEM00900 AEM00901

### **6.2. Source Level Configuration**

	Voltage Level							
	SRC_LVL_CFG[5:0]							
L	L	L	Н	Н	L	0.12 V		
L	L	L	Н	Н	Н	0.13 V		
L	L	Н	L	L	L	0.15 V		
L	L	Н	L	L	Н	0.16 V		
L	L	Н	L	Н	L	0.18 V		
L	L	Н	L	Н	Н	0.19 V		
L	L	Н	Н	L	L	0.21 V		
L	L	Н	Н	L	Н	0.22 V		
L	L	Н	Н	Н	L	0.24 V		
L	L	Н	Н	Н	Н	0.25 V		
L	Н	L	L	L	L	0.27 V		
L	Н	L	L	L	Н	0.28 V		
L	Н	L	L	Н	L	0.30 V		
L	Н	L	L	Н	Н	0.33 V		
L	Н	L	Н	L	L	0.36 V		
L	Н	L	Н	L	Н	0.39 V		
L	Н	L	Н	Н	L	0.42 V		
L	Н	L	Н	Н	Н	0.45 V		
L	Н	Н	L	L	L	0.48 V		
L	Н	Н	L	L	Н	0.51 V		
L	Н	Н	L	Н	L	0.54 V		
L	Н	Н	L	Н	Н	0.57 V		
L	Н	Н	Н	L	L	0.60 V		
L	Н	Н	Н	L	Н	0.63 V		
L	Н	Н	Н	Н	L	0.66 V		
L	Н	Н	Н	Н	Н	0.69 V		

	Voltage Level							
	SRC_LVL_CFG[5:0]							
Н	L	L	L	L	L	0.72 V		
Н	L	L	L	L	Н	0.75 V		
Н	L	L	L	Н	L	0.78 V		
Н	L	L	L	Н	Н	0.81 V		
Н	L	L	Н	L	L	0.84 V		
Н	L	L	Н	L	Н	0.87 V		
Н	L	L	Н	Н	L	0.90 V		
Н	L	L	Н	Н	Н	0.93 V		
Н	L	Н	L	L	L	0.96 V		
Н	L	Н	L	L	Н	0.99 V		
Н	L	Н	L	Н	L	1.02 V		
Н	L	Н	L	Н	Н	1.05 V		
Н	L	Н	Н	L	L	1.08 V		
Н	L	Н	Н	L	Н	1.11 V		
Н	L	Н	Н	Н	L	1.14 V		
Н	L	Н	Н	Н	Н	1.17 V		
Н	Н	L	L	L	L	1.20 V		
Н	Н	L	L	L	Н	1.23 V		
Н	Н	L	L	Н	L	1.26 V		
Н	Н	L	L	Н	Н	1.29 V		
Н	Н	L	Н	L	L	1.32 V		
Н	Н	L	Н	L	Н	1.35 V		
Н	Н	L	Н	Н	L	1.38 V		
Н	Н	L	Н	Н	Н	1.41 V		
Н	Н	Н	L	L	L	1.44 V		
Н	Н	Н	L	L	Н	1.47 V		

Table 5: Configuration of SRC\_LVL\_CFG[5:0]

The source voltage regulation can be configured using GPIO or  $I^2C$  communication.

Six dedicated configuration pins, SRC\_LVL\_CFG[5:0], allow selecting the  $V_{SRC,REG}$  at which the source regulates its voltage. All configurations set below SRC\_LVL\_CFG[LLLHHL] will be set at 0.12 V.

The  $\rm I^2C$  communication allows more precision than the GPIO configuration (see Section 9.2), as SRCREGU.VALUE (0x01) is a 7-bit register.

# **6.3. Storage Element Thresholds Configuration**

The user must set the voltage thresholds for which the storage element is considered to be discharged ( $V_{OVDIS}$ ) and fully charged ( $V_{OVCH}$ ).

 $V_{OVDIS}$  is configured on the VOVDIS (0x02) register and encoded on 6 bits. The value to be written to the register is determined using the following equation:

$$THRESH = \frac{V_{OVDIS} - 0.50625}{0.05625}$$





THRESH is the integer value to be written in the register. The minimum value is 2.8 V. If the register value corresponds to  $V_{OVDIS}$  < 2.8 V, the threshold voltage is forced to 2.8 V.

V<sub>OVCH</sub> is configured on the VOVCH (0x03) register and encoded on 6 bits. The value to be written to the register is determined using the following equation:

THRESH = 
$$\frac{V_{OVCH} - 1.2375}{0.05625}$$

THRESH is the integer value to be written in the register. The minimum value is 3.0 V. If the register value corresponds to  $V_{OVCH}$  < 3.0 V, the threshold voltage is forced to 3.0 V.

It is also possible to configure  $V_{OVDIS}$  and  $V_{OVCH}$  with configuration pins STO\_CFG[2:0] as shown in Table 6.

Configuration	Storage elem	Storage element threshold	
STO_CFG[2:0]	V <sub>OVCH</sub>	V <sub>OVDIS</sub>	
LLL	4.50 V	3.30 V	NiCd 3 cells
LLH	4.00 V	2.80 V	Tadrian TLI1020A
LHL	3.63 V	2.80 V	LiFePO4
LHH	3.90 V	2.80 V	Tadrian HLC1020
HLL	3.90 V	3.50 V	Li-ion (ultra long life)
HLH	3.90 V	3.01 V	Li-ion (long life)
HHL	4.35 V	3.01 V	LiPo
ннн	4.12 V	3.01 V	Li-ion/solid-state/ NiMH

Table 6: Usage of STO\_CFG[2:0]

DISCLAIMER: the provided storage element thresholds in the table above are indicative to support a wide range of storage element variants. They are provided as is to the best knowledge of e-peas's application laboratory. They should not replace the actual values provided in the storage element manufacturer's specifications and datasheet.

## 6.4. Disable Storage Element Charging

Pulling up DIS\_STO\_CH to  $V_{STO}$  disables the charging of the storage element connected to STO. The storage element charging can also be disabled via  $I^2C$  by setting the PWR.STOCHDIS register.

Please note that, if the keep-alive feature is enabled by pulling up KEEP\_ALIVE to V<sub>INT</sub>, VINT is supplied by STO regardless of the setting of DIS\_STO\_CH. To make sure that the storage element is neither charged nor used to supply VINT, user must tie both DIS\_STO\_CH to STO and KEEP\_ALIVE to GND.





### 6.5. External Components

#### 6.5.1. Storage Element

The storage element of the AEM0090x must be a rechargeable battery, which size should be chosen so that its voltage does not fall below V<sub>OVDIS</sub> for longer than 2.5 s during current draw from the battery to the load connected on it. To keep the chip functionality, minimum voltage on STO pin shall remain above 2.8V.

The monitoring of the storage element is done periodically. It is therefore possible that the storage element may be overloaded if it is incorrectly sized.

It is mandatory to buffer the battery with a capacitor  $C_{STO}$  if the internal resistance of the battery is high, to ensure that the current pulled from the battery by the application circuit does not ever make the battery voltage fall below 2.8 V.

A minimal decoupling capacitor of 22  $\mu F$  is recommended to obtain optimal DCDC converter efficiency when using high ESR battery, or when measuring efficiency using laboratory equipments such as source measurement units (SMU).

#### 6.5.2. External Inductor Information

#### LDCDC

The AEM0090x operates with one standard miniature inductor. L<sub>DCDC</sub> must comply to the following:

- Peak current rating must be at least 1 A for a 3.3 µH inductor in high-power mode and 500 mA if highpower mode is disabled. Current rating decreases linearly when inductor value increases.
- Switching frequency must be at least 10 MHz.
- ESR as low as possible as it has a strong influence on DCDC efficiency.
- The recommended values for optimal efficiency is:
  - 6.8 μH for AEM00900
  - 33 μH for AEM00901

#### 6.5.3. External Capacitors Information

#### CSRC

This capacitor acts as an energy buffer at the input of the boost converter. It prevents large voltage variations when the buck-boost converter is active. The recommended value is  $10\,\mu\text{F}$ .

#### CINT

This capacitor acts as an energy buffer for the internal voltage supply. The minimum effective value is 3.3  $\mu F$ . 22 $\mu F$  is recommended.

### $\mathbf{C}_{\text{STO}}$

This capacitor allows for buffering the current peaks of the boost converter output.

# 6.5.4. Optional External Components for Thermal Monitoring

The following components are required for the thermal monitoring:

- One resistor, typ. 22 k $\Omega$  ±20% (PNRC0402FR-0722KL)
- One NTC thermistor, typ. R0 = 10 k $\Omega$  ±5% and Beta = 3380 K ±3% (NCP15XH103J03RC)

# 6.5.5. Optional Pull-up Resistors for the I<sup>2</sup>C Interface

SDA and SCL must be pulled up by resistors (1  $k\Omega$  typical) if the  $l^2C$  interface is used. The value must be determined according to the  $l^2C$  mode used.





## 7. I<sup>2</sup>C Serial Interface Protocol

The AEM0090x uses I<sup>2</sup>C communication for configuration as well as to provide information about system status and measurement data. Communication requires a serial data line (SDA) and a serial clock line (SCL). A device sending data is defined as a transmitter and a device receiving data as a receiver. The device that controls the communication is called a master and the device it controls is defined as the slave.

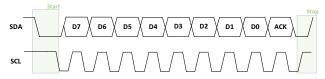


Figure 10: I<sup>2</sup>C transmission frame

The master is in charge of generating the clock, managing bus accesses and generating the start and stop bits. The AEM0090x is a slave that will receive configuration data or send the informations requested by the master.

The AEM0090x supports I<sup>2</sup>C Standard-mode (100 kHz maximum clock rate), Fast-mode (400 kHz maximum clock rate), and Fast-mode Plus (1 MHz maximum clock rate) device. Data are sent with the most significant bit first.

Here are some typical I<sup>2</sup>C interface states:

- When the communication is idle, both transmission lines are pulled up (SDA and SCL are open drain outputs);
- Start bit (S): to initiates the transmission, the master switches the SDA line low while keeping SCL high. This is called the start bit;
- Stop bit (P): to end the transmission, the master switches the SDA line from low to high while keeping SCL high. This is called a stop bit;
- Repeated Start bit (Sr): it is used as a back-to-back start and stop bit. It is similar to a start condition, but when the bus is not on idle;
- ACK: to acknowledge a transmission, the device receiving the data (master in case of a read mode transmission, slave in case of a write mode transmission) switches SDA low;
- NACK: when the device receiving data keeps SDA high after the transmission of a byte. When reading a byte, this can mean that the master is done reading bytes from the slave.

To initiate the communication, the master sends a byte with the following informations:

- Bits [7:1] is the slave address, which is 0x41;

- Bit [0] is the communication mode: 1 for 'read mode' (used when the master reads informations from the slave) and 0 for 'write mode' (when the master writes informations to the slave);
- Slave replies with an ACK to acknowledge that the address has been successfully transmitted.

Here is the procedure for the master to write a slave register:

- Master sends the address of the slave in 'write' mode;
- Slave sends an ACK;
- Master sends the address of the register to be written. For example, for the TEMPCOLD register, the master sends the value 0x04;
- Slave sends an ACK;
- Master sends the data to write to the register;
- Slave sends an ACK;
- If the master wants to write register at the next address (TEMPHOT in our example), it sends next value to write, without having to specify the address again. This can be done several times in a row for writing several consecutive registers;
- Else the master sends a stop bit (P).

Here is the procedure for the master to read a slave register:

- Master sends the address of the slave in 'write' mode;
- Slave sends an ACK;
- Master sends the address of the register to be read.
   For example, for the SRC\_REGU register, the master sends the value 0x01;
- Slave sends an ACK;
- Master sends a repeated start bit (Sr);
- Master sends the address of the slave in 'read' mode;
- Slave sends an ACK;
- Master provides the clock on SCL to allow the slave to shift the data of the read register on SDA;
- If the master wants to read register at the next address (VOVDIS in our example), it sends an ACK and provides the clock for the slave to shift its following 8 bits of data. This can be done several times in a row for reading several registers;
- If the master wants to end the transmission, it sends a NACK to notify the slave that the transmission is over, and then sends a stop bit (P).

Both communications are described in the Figure 11. Refer to Table 7 for all register addresses.



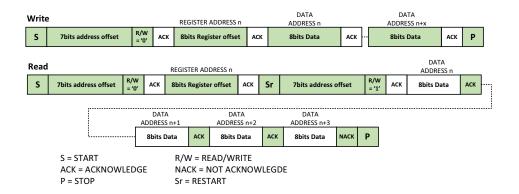


Figure 11: Read and write transmission





# 8. Registers Map

Address	Name	Bit	Field Name	Access	RESET	Description
0x00	VERSION	[3:0]	MINOR	R		Chip ID
UXUU	VERSION	[7:4]	MAJOR	_	_	Chip ib
0x01	SRCREGU	[7:0]	VALUE	R/W	0x77 (1.47V)	Source voltage regulation
0x02	VOVDIS	[5:0]	THRESH	R/W	0x2D (3.05V)	Overdischarge level of the storage element
0x03	VOVCH	[5:0]	THRESH	R/W	0x33 (4.1V)	Overcharge level of the storage element
0x04	TEMPCOLD	[7:0]	THRESH	R/W	0x8F (0°C)	Cold temperature level
0x05	TEMPHOT	[7:0]	THRESH	R/W	0x2F (45°C)	Hot temperature level
		[0:0]	KEEPALEN	R/W	0x01	Keepalive enable
0x06	PWR	[1:1]	HPEN	R/W	0x01	AEM00900: high-power mode enable AEM00901: Reserved
		[2:2]	TMONEN	R/W	0x01	Temperature monitoring enable
		[3:3]	STOCHDIS	R/W	0x00	Battery charging disable
0x07	SLEEP	[0:0]	EN	R/W	0x01	Sleep mode enable
UXU7	SLEEP	[3:1]	SRCTHRESH	R/W	0x00	SRC LOW threshold
0x08	STOMON	[2:0]	RATE	R/W	0x00	ADC rate
		[0:0]	EN	R/W	0x00	APM enable
0x09	APM	[1:1]	RSVD1	R/W	0x00	Write 0x01 when APM is used
		[3:2]	RSVD2	R/W	0x00	Write 0x00 when APM is used
		[0:0]	I2CRDY	R/W	0x01	IRQ serial interface ready enable
		[1:1]	VOVDIS	R/W	0x00	IRQ STO OVDIS enable
		[2:2]	VOVCH	R/W	0x00	IRQ STO OVCH enable
0x0A	IRQEN	[3:3]	SRCTHRESH	R/W	0x00	IRQ SRC LOW enable
		[4:4]	TEMP	R/W	0x00	IRQ temperature enable
		[5:5]	APMDONE	R/W	0x00	IRQ APM done enable
0x0B	CTRL	[0:0]	UPDATE	R/W	0x00	Load I <sup>2</sup> C registers configuration
UXUB	CIKE	[2:2]	SYNCBUSY	R	0x00	Synchronization busy flag
		[0:0]	I2CRDY	R	0x00	IRQ serial interface ready flag
		[1:1]	VOVDIS	R	0x00	IRQ STOR OVDIS flag
		[2:2]	VOVCH	R	0x00	IRQ STOR OVCH flag
0x0C	IRQFLG	[3:3]	SRCTHRESH	R	0x00	IRQ SRC LOW flag
		[4:4]	TEMP	R	0x00	IRQ temperature flag
		[5:5]	APMDONE	R	0x00	IRQ APM done flag
		[1:1]	VOVDIS	R	0x00	Status STO OVDIS
		[2:2]	VOVCH	R	0x00	Status STO OVCH
0x0D	STATUS	[3:3]	SRCTHRESH	R	0x00	Status SRC LOW
UXUD	314103	[4:4]	TEMP	R	0x00	Status temperature
		[6:6]	CHARGE	R	0x00	Status STO CH
		[7:7]	BSTDIS	R	0x00	Status BST DIS GPIO
0x0E	APM0	[7:0]	DATA	R	0x00	APM data 0
0x0F	APM1	[7:0]	DATA	R	0x00	APM data 1
0x10	APM2	[7:0]	DATA	R	0x00	APM data 2
0x11	TEMP	[7:0]	DATA	R	0x00	Temperature data
0x12	STO	[7:0]	DATA	R	0x00	Battery voltage
0x13	RSVD	[7:0]	-	R	-	Reserved

Table 7: Register summary





# 9. Registers Configurations

# 9.1. Version Register (VERSION)

The VERSION register holds the version of the chip, with major and minor revision numbers.

VERSION Register	0x00 R
Bit [7:4]	Bit [3:0]
MAJOR	MINOR
0x00	0x00

Table 8: VERSION register

Bit [7:4]: major revision number (VERSION.MAJOR).

Bit [3:0]: minor revision number (VERSION.MINOR).





# 9.2. Source Voltage Regulation Register (SRCREGU)

The source voltage regulation can be set thanks to the  $I^2C$  communication with more precision. The register is made of 7 bits. Use the Table 9 to set the SRCREGU.VALUE register according the desired  $V_{SRC,REG}$ .

SRCREGU .DATA [7:0]	V <sub>SRC,REG</sub> [V]	SRC .DATA [7:0]	V <sub>SRC,REG</sub> [V]	SRC .DATA [7:0]	V <sub>SRC,REG</sub> [V]	SRC .DATA [7:0]	V <sub>SRC,REG</sub> [V]
0x00	Source	0x25	0.300	0x40	0.705	0x5B	1.110
	Low <sup>1</sup>	0x26	0.315	0x41	0.720	0x5C	1.125
0x0C		0x27	0.330	0x42	0.735	0x5D	1.140
0x0D	0.120	0x28	0.345	0x43	0.750	0x5E	1.155
0x0E	0.1275	0x29	0.360	0x44	0.765	0x5F	1.170
0x0F	0.135	0x2A	0.375	0x45	0.780	0x60	1.185
0x10	0.1425	0x2B	0.390	0x46	0.795	0x61	1.200
0x11	0.150	0x2C	0.405	0x47	0.810	0x62	1.215
0x12	0.1575	0x2D	0.420	0x48	0.825	0x63	1.230
0x13	0.165	0x2E	0.435	0x49	0.840	0x64	1.245
0x14	0.1725	0x2F	0.450	0x4A	0.855	0x65	1.260
0x15	0.180	0x30	0.465	0x4B	0.870	0x66	1.275
0x16	0.1875	0x31	0.480	0x4C	0.885	0x67	1.290
0x17	0.195	0x32	0.495	0x4D	0.900	0x68	1.305
0x18	0.2025	0x33	0.510	0x4E	0.915	0x69	1.320
0x19	0.210	0x34	0.525	0x4F	0.930	0x6A	1.335
0x1A	0.2175	0x35	0.540	0x50	0.945	0x6B	1.350
0x1B	0.225	0x36	0.555	0x51	0.960	0x6C	1.365
0x1C	0.2325	0x37	0.570	0x52	0.975	0x6D	1.380
0x1D	0.240	0x38	0.585	0x53	0.990	0x6E	1.395
0x1E	0.2475	0x39	0.600	0x54	1.005	0x6F	1.410
0x1F	0.255	0x3A	0.615	0x55	1.020	0x70	1.425
0x20	0.2625	0x3B	0.630	0x56	1.035	0x71	1.440
0x21	0.270	0x3C	0.645	0x57	1.050	0x72	1.455
0x22	0.2775	0x3D	0.660	0x58	1.065	0x73	1.470
0x23	0.285	0x3E	0.675	0x59	1.080		1.470
0x24	0.2925	0x3F	0.690	0x5A	1.095	0x75	1.470

Table 9: SRCREGU register (0x01)

1.Setting SRCREGU.DATA to a value lower than 0x0D causes the AEM0090x to consider the SRC voltage to be lower than SLEEP.SRCTHRESHSLEEP STATE if the SLEEP condition is met.

To find the other correlations between the voltages and the values to put in the register, the user can use those formulas:

If the desired V<sub>SRC,REG</sub> is between 0.12V and 0.30V:

$$VALUE = \frac{V_{SRC, REG} - 0.0225}{0.0075}$$

If the desired V<sub>SRC,REG</sub> is between 0.30V and 1.47V:

$$VALUE = \frac{V_{SRC, REG} + 0.255}{0.015}$$

If SRCREG.VALUE is set to 0b0001100 and that SLEEP.EN is set, the AEM0090x switches to SLEEP STATE.





# 9.3. Storage Element Threshold Registers (VOVDIS, VOVCH)

The configuration of the storage element thresholds is done by setting two different registers through the  $I^2C$  communication:

- The V<sub>OVDIS</sub> threshold is configured in register VOVDIS (0x02):
- The V<sub>OVCH</sub> threshold is configured in register VOVCH (0x03).

The information about the storage element threshold voltage is available on section 6.3.



## 9.4. Temperature Register (TEMPCOLD, TEMPHOT)

The configuration of the temperature thresholds is done by setting two registers through I<sup>2</sup>C communication:

- The low temperature threshold is configured in register TEMPCOLD (0x04);
- The high temperature threshold is configured in register TEMPHOT (0x05).

The temperature protection uses a voltage divider consisting of the resistor  $R_{\text{DIV}}$  and the thermistor  $R_{\text{TH}}(T)$ . Considering the specifications of the thermistor used, it is possible to determine the relationship between the temperature and the resistance of the thermistor. The following equation must therefore be applied to determine the value to be written to the register:

THRES = 
$$256 \cdot \frac{R_{TH}(T)}{R_{TH}(T) + R_{DIV}}$$

The equation is the same for both the high and the low thresholds. THRESH is the value to be written to the registers,  $R_{TH}(T)$  is the resistance of the thermistor at the threshold temperature and  $R_{DIV}$  is the resistance that creates a resistive divider with  $R_{TH}(T)$ , as shown on Figure 8. The AEM0090x determines if the ambient temperature is within the range previously set by measuring the voltage on pin TH\_MON.

#### **9.4.1. TEMPCOLD**

Minimum temperature (cold) for storage element charging register.

TEMPCOLD Register	0x04	R/W
	Bit [7:0]	
	THRESH	
	0x8F	

Table 10: TEMPCOLD register

The following equations are useful to determine the temperature from the THRES register field value:

$$\begin{split} R_{TH}(T) &= R0 \cdot e^{B \cdot \left(\frac{1}{T} - \frac{1}{T_0}\right)} \\ T &= \frac{B}{In\left(\frac{R_{TH}(T)}{R0}\right) + \frac{B}{T_0}} \end{split}$$

- THRESH is the unsigned 8-bit value to be written in the registers to set the temperature threshold to the temperature T [K].
- R0 [ $\Omega$ ] is the resistance of the NTC thermistor at ambient temperature T<sub>0</sub> = 298.15 K (25 °C).
- $R_{TH}(T)$  [ $\Omega$ ] is the resistance of the thermistor at temperature T [K].
- T<sub>0</sub> [K] = 298.15 K (25 °C)
- T [K] is the current ambient temperature of the
- B is the characteristic constant of the thermistor, allowing to determine the resistance of the thermistor for a given temperature.

For example with a Murata NCP15XH103J03RC the default thresholds are 0°C and 45°C (see Table 7), which matches the specifications of most Li-lon batteries.

#### Bit [7:0]: THRESH (TEMPCOLD.THRESH).

This fields is used to configure the minimum temperature (cold) threshold.





### **9.4.2. TEMPHOT**

Maximum temperature (hot) for storage element charging register.

TEMPHOT Register	0x05	R/W
	Bit [7:0]	
	ТНКЕЅН	
	0x2F	

Table 11: TEMPHOT register

### Bit [7:0]: THRESH (TEMPHOT.THRESH).

This fields is used to configure the maximum temperature (hot) threshold.





## 9.5. Power Register (PWR)

The PWR (0x06) register is dedicated to the power settings of the AEM0090x and is made of 4 bits:

PWR Register	0x06		R/W	
Bit [7:4]	Bit [3]	Bit [2]	Bit [1]	Bit [0]
RESERVED	STOCHDIS	TMONEN	AEM00900: HPEN AEM00901: Reserved	KEEPALEN
0x00	0	1	1	1

Table 12: PWR register

#### Bit [3]: Battery charging disable (PWR.STOCHDIS).

Prevent charging the battery.

- 0: DIS allow the charging of the battery
- 1: EN disable the charging of the battery.

The charging of the battery is disabled if either PWR.STOCHDIS is set or if the DIS\_STO\_CH pin is HIGH. The state of the DIS\_STO\_CH pin is not ignored when the AEM0090x switches to the I<sup>2</sup>C register configuration (see Section 6.1), as it would for all other configuration pins.

#### Bit [2]: Temperature monitoring enable (PWR.TMONEN).

The temperature monitoring enable bit enables the monitoring of the ambient temperature.

- 0: DIS Disable the temperature monitoring.
- 1: EN Enable the temperature monitoring.

#### Bit [1]: High-power mode enable (PWR.HPEN).

Allow the AEM to automatically enter high-power mode if needed, allowing for more power to be harvested from SRC (see section 5.5.).

- 0: DIS Disable automatic high-power mode.
- 1: EN Enable automatic high-power mode.

NOTE: the PWR.HPEN field is only available on the AEM00900 and is reserved on the AEM00901.

#### Bit [0]: Keep-alive enable (PWR.KEEPALEN).

Define the energy source from which the AEM0090x supplies VINT (internal circuitry).

- O: DIS VINT is supplied by SRC through the boost converter.
- 1: EN VINT is supplied by STO.

Refer to section 5.6. for more information.

NOTE: disabling the keep-alive feature is not recommended when configuring the AEM0090x with I<sup>2</sup>C registers, see Section 5.6.





# 9.6. Sleep Register (SLEEP)

The Sleep register SLEEP (0x07) enables the sleep mode and sets the conditions for entering the sleep mode.

SLEEP Register	0x07 R/W	
Bit [7:4]	Bit [3:1]	Bit [0]
RESERVED	SRCTHRESH	EN
0x00	0x00	1

Table 13: SLEEP register

#### Bit [3:1]: Sleep threshold (SLEEP.SRCTHRESH)

This field sets the voltage threshold below which the AEM0090x enters SLEEP STATE. Table 14 shows the available settings.

For example, if the SLEEP.SLPTHRESH field is set to 010, the AEM will switch to SLEEP STATE if the source target voltage is set below 0.255 V.

SLEEP.SRCTHRESH				
Configuration	SRC threshold			
0x00	0.105 V			
0x01	0.202 V			
0x02	0.255 V			
0x03	0.300 V			
0x04	0.360 V			
0x05	0.405 V			
0x06	0.510 V			
0x07	0.600 V			

Table 14: Configuration of the sleep threshold

#### Bit [0]: Sleep mode enable (SLEEP.EN)

This field controls the SLEEP STATE behavior of the AEM0090x.

- 0: DIS The AEM0090x will never switch to SLEEP STATE.
- 1: EN Enable the AEM0090x to switch to SLEEP STATE if conditions are met (see below).

The SRC threshold is set by default at 0.105 mV.





# 9.7. Storage Element Acquisition Rate Register (STOMON)

This field (STOMON, 0x08) configures the acquisition rate of the ADC that measures STO voltage. Depending on the application, the source and the storage element, the user might want to increase the frequency of the acquisitions of the battery voltage, so that the acquisition rate is significantly faster than the expected voltage variation on the battery. Increasing this frequency increases the energy consumption of the AEM0090x.

STOMON Register (0x08)					
Configuration	Sampling rate	Additional consumption on storage element (typ.)			
0x00	Every 1.024 s	0.4 nA			
0x01	Every 512 ms	0.8 nA			
0x02	Every 256 ms	1.6 nA			
0x03	Every 128 ms	3.2 nA			
0x04	Every 64 ms	6.4 nA			

Table 15: Acquisition rates for STO ADC





# 9.8. Average Power Monitoring Control Register (APM)

Average Power Monitoring (APM; register address 0x09) allows for estimating the energy transferred from the source to the battery.

APM Register	0x09	R/W	
Bit [7:4]	Bit [3:2]	Bit [1]	Bit [0]
RESERVED	RSVD2	RSVD1	EN
0x00	0x00	0	0

Table 16: APM register

#### Bit [3:2]: Reserved 2 (APM.RSVD2)

Always write 0x00 to this register field when the APM is used.

### Bit [1]: Reserved 1 (APM.RSVD1)

Always write 0x01 to this register field when the APM is used.

#### Bit [0]: APM enable (APM.EN)

This field enables the APM feature.

- 0: DIS APM feature disabled.
- 1: EN APM feature enabled.





## 9.9. IRQ Enable Register (IRQEN)

Interrupts enable register: configures on which event the IRQ pin is set HIGH.

IRQEN	l Registe	er		0x0A		R/W	
Bit	Bit	Bit	Bit	Bit	Bit	Bit	Bit
[7]	[6]	[5]	[4]	[3]	[2]	[1]	[0]
RESERVED	APMERR	APMDONE	TEMP	SRCTHRESH	НЭЛОЛ	SIGNON	I2CRDY
0	0	0	0	0	0	0	1

Table 17: IRQEN register

#### Bit [6]: IRQ APM error enable (IRQEN.APMERR)

Enable the IRQ pin to be asserted (HIGH) when an APM error occurs

- 0: DIS Disable.
- 1: EN Enable.

#### Bit [5]: IRQ APM done enable (IRQEN.APMDONE)

Enable the IRQ pin to be asserted (HIGH) when APM data is available.

- 0: DIS Disable.
- 1: EN Enable.

#### Bit [4]: IRQ temperature enable (IRQEN.TEMP)

Enable the IRQ pin to be asserted (HIGH) when the temperature crosses the minimum or maximum temperature allowed to charge the battery (see section 9.4.).

- 0: DIS Disable.
- 1: EN Enable.

#### Bit [3]: IRQ source low enable (IRQEN.SRCTHRESH)

Enable the IRQ pin to be asserted (HIGH) when  $V_{\text{SRC},\text{REG}}$  crosses the SRC LOW threshold.

- 0: DIS Disable.
- 1: EN Enable.

#### Bit [2]: IRQ storage overcharge enable (IRQEN.VOVCH)

Enable the IRQ pin to be asserted (HIGH) when the battery voltage crosses the  $V_{OVCH}$  threshold.

- 0: DIS Disable.
- 1: EN Enable.

#### Bit [1]: IRQ storage overdischarge enable (IRQEN.VOVDIS)

Enable the IRQ pin to be asserted (HIGH) when the storage element voltage crosses the V<sub>OVDIS</sub> threshold.

- 0: DIS Disable.
- 1: EN Enable.

#### Bit [0]: IRQ serial interface ready enable (IRQEN.I2CRDY)

This bit is set at 1 by default.

When the AEM0090x has coldstarted and is ready to communicate through I<sup>2</sup>C. The IRQ pin is asserted (HIGH).

- 0: DIS AEM0090x not ready to communicate through the  $I^2C$  bus.
- 1: EN AEM0090x ready to communicate through the  $\mbox{I}^2\mbox{C}$  bus.





## 9.10. I<sup>2</sup>C Control (CTRL)

Control register.

CTRL Register 0x0B		R/W	
Bit [7:3]	Bit [2]	Bit [1]	Bit [0]
RESERVED	SYNCBUSY	RESERVED	UPDATE
0x00	0	0	0

Table 18: CTRL register

#### Bit [2]: SYNCBUSY (CTRL.SYNCBUSY).

This field indicates whether the synchronization from the I<sup>2</sup>C registers to the system registers is ongoing or not. While ongoing, it is not possible to write in the registers.

- 0: NSYNC R: CTRL register not synchronizing.
- 1: SYNC R: CTRL register synchronizing.

#### Bit [0]: UPDATE (CTRL.UPDATE).

This field is used to control the source of the AEM0090x configuration (GPIO or I<sup>2</sup>C).

Furthermore, this field is used to update the AEM0090x configuration with the current configuration from the I<sup>2</sup>C registers.

- 0: GPIO
  - W: load configurations from the GPIO.
  - R: configurations from the GPIO is currently used if read as 0.
- 1: I2C
  - W: load configurations from the I<sup>2</sup>C registers.
  - R: configurations from the I<sup>2</sup>C is currently used if read as 1.

NOTE: writing any register does not have any effect until 1 is written to the CTRL.UPDATE field, leading to the AEM0090x to read the new register values and apply them.

NOTE: when using I<sup>2</sup>C register configuration, user can switch back to GPIO configuration by writing 0 to the CTRL.UPDATE field. In that case, the settings previously written to the IRQEN registers are still valid even when using GPIO configuration, as well as the data in IRQFLG register.





## 9.11. IRQ Flag Register (IRQFLG)

The IRQFLG (0x0C) register contains all interrupt flags, corresponding to those enabled in the IRQEN register.

This register is reset when read.

IRQFL	G Regist	ter		0x0C		R	
Bit [7]	Bit [6]	Bit [5]	Bit [4]	Bit [3]	Bit [2]	Bit [1]	Bit [0]
RESERVED	APMERR	APMDONE	TEMP	SRCTHRESH	<b>VOVCH</b>	VOVDIS	12CRDY
0	0	0	0	0	0	0	1

Table 19: IRQFLG register

### Bit [6]: IRQ APM error Flag (IRQFLG.APMERR)

This interrupt flag is set when an APM error occurred.

- 0: NFLG No interrupt flag raised.
- 1: FLG Interrupt flag raised.

### Bit [5]: IRQ APM done Flag (IRQFLG.APMDONE)

This interrupt flag is set when APM data is available.

- 0: NFLG No interrupt flag raised.
- 1: FLG Interrupt flag raised.

### Bit [4]: IRQ temperature Flag (IRQFLG.TEMP)

This interrupt flag is set when the temperature crosses the minimum or maximum temperature (selected through the TEMPCOLD and TEMPHOT registers).

- 0: NFLG No interrupt flag raised.
- 1: FLG Interrupt flag raised.

### Bit [3]: IRQ source low Flag (IRQFLG.SRCTHRESH)

This interrupt flag is set when  $V_{SRC,REG}$  crosses the SRC LOW voltage (112mV).

- 0: NFLG No interrupt flag raised.
- 1: FLG Interrupt flag raised.

### Bit [2]: IRQ storage overcharge Flag (IRQFLG.VOVCH)

This interrupt flag is set when the battery crosses the overcharge voltage (selected through the VOVCH register).

- 0: NFLG No interrupt flag raised.
- 1: FLG Interrupt flag raised.

### Bit [1]: IRQ storage overdischarge Flag (IRQFLG.VOVDIS)

This interrupt flag is set when the battery crosses the overdischarge voltage (selected through the VOVDIS register).

- 0: NFLG No interrupt flag raised.
- 1: FLG Interrupt flag raised.

#### Bit [0]: IRQ serial interface ready Flag (IRQFLG.I2CRDY)

This interrupt flag is set when the AEM0090x has coldstarted and is ready to communicate through I<sup>2</sup>C (the corresponding interrupt source is enabled by default).

- 0: NFLG No interrupt flag raised.
- 1: FLG Interrupt flag raised.





## 9.12. Status Register (STATUS)

The STATUS (0x0D) register contains informations about the status of the AEM0090x.

STATU	STATUS Register			0x0D		R	
Bit [7]	Bit [6]	Bit [5]	Bit [4]	Bit [3]	Bit [2]	Bit [1]	Bit [0]
BSTDIS	CHARGE	RESERVED	TEMP	SRCTHRESH	ЛОУСН	VOVDIS	RESERVED
0	0	0	0	0	0	0	0

Table 20: Status register

### Bit [7]: Status BSTDIS (STATUS.BSTDIS)

This status indicates whether the storage charging is enabled or not via the GPIO. If this bit is set to 0, the storage element charging is enabled. If it is set to 1, the storage element charging is disabled.

### Bit [6]: Status STO CH (STATUS.CHARGE)

This status indicates whether the AEM is currently charging the battery or not. If this bit is set to 0, the boost is running. If it is set to 1, the boost is not running. Set condition:

& (OVDIS STATE | SUPPLY STATE | SHUTDOWN STATE)

### Bit [4]: Temperature Status (STATUS.TEMP)

This bit is set to 1 if the ambient temperature is outside the range defined by the TEMPCOLD and TEMPHOT registers. It is set to 0 is the temperature is within this range.

### Bit [3]: Status SRC LOW (STATUS.SRCTHRESH)

This status indicates whether the source target voltage is higher or lower than the sleep level threshold (112mV). If the source target voltage is higher than the sleep level then the field is set to 0, else the field is set to 1.

### Bit [2]: Status STOR OVCH (STATUS.VOVCH)

This status indicates whether the battery voltage is higher or lower than the overcharge level threshold. If the battery voltage rises above V<sub>OVCH</sub> then the field is set to 1, else it is set to 0.

### Bit [1]: Status STOR OVDIS (STATUS.VOVDIS)

This status indicates whether the battery is higher or lower than the overdischarge level threshold. If the battery voltage goes below V<sub>OVDIS</sub> then the field is set to 1, else it is set to 0.





## 9.13. Average Power Monitoring Data Registers (APM)

The APM (0x0E, 0x0F, 0x10) registers contain the Average Power Monitoring data.

APM0 Register (0x0E)							
Bit [7]	Bit [6]	Bit [5]	Bit [4]	Bit [3]	Bit [2]	Bit [1]	Bit [0]
DATA[7:0]							

APM1 Register (0x0F)							
Bit	Bit	Bit	Bit	Bit	Bit	Bit	Bit
[7] [6] [5] [4] [3] [2] [1] [0]							
DATA[15:8]							

APM2 Register (0x10)							
Bit	Bit	Bit	Bit	Bit	Bit	Bit	Bit
[7]	[6]	[5]	[4]	[3]	[2]	[1]	[0]
SHIFT[3:0]				DATA[19:16]			

Table 21: APM registers





## 9.14. Temperature Data Register (TEMP)

This field contains the result of the ADC acquisition for the temperature monitoring. The voltage at the terminals of the voltage divider can be derived by applying the following equation, with  $V_{REF} = 1 \text{ V}$ :

$$V_{TH} = \frac{V_{REF} \cdot DATA}{256}$$

Or, in order to make a comparison with the Table in the thermistor datasheet, it is possible to find the impedance of the thermistor:

D	=	D .	DATA		
TH	_	DIV	256 – E	ATA	

TEMP Register	0x11	R
	Bit	
	[7:0]	
	DATA	
	0x00	

Table 22: TEMP register





## 9.15. Battery Voltage Register (STO)

The STO (0x12) contains the 8-bit result from the ADC acquisition of the battery voltage. To convert the result to Volts, the following equation is applied.

$$V_{STO} = \frac{4.8 \text{ V} \cdot \text{DATA}}{256}$$

STO Register	0x12	R	
	Bit [7:0]		
	DATA		
	0x00		

Table 23: STO register





## 10. Typical Application Circuits

## 10.1. Example Circuit 1

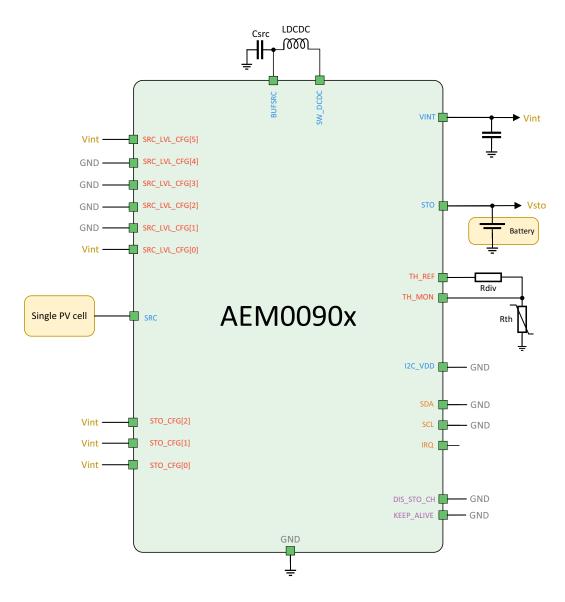


Figure 12: Typical application circuit 1

The circuit is an example of a system with solar energy harvesting with the AEM0090x. It uses a Li-ion rechargeable battery as energy storage.

- Energy source: PV cell.
- SRC\_LVL\_CFG[5:0] = HLLLLH: The source voltage regulation is set to 0.75 V to extract the maximum power of the PV cell.
- STO\_CFG[2:0] = HHH: The storage element is a Li-ion battery.

- V<sub>OVCH</sub> = 4.12 V
- V<sub>OVDIS</sub> = 3.01 V
- The thermal monitoring is used with a default threshold value (TEMPCOLD = 0°C, TEMPHOT = 45°C) with  $R_{DIV}$  = 22 k $\Omega$  and  $R_{TH}$ : NCP15XH103J03RC.
- The I<sup>2</sup>C communication is not used.
- DIS\_STO\_CH is connected to GND: The charging of the storage element on STO is enabled.

## 10.2. Example Circuit 2

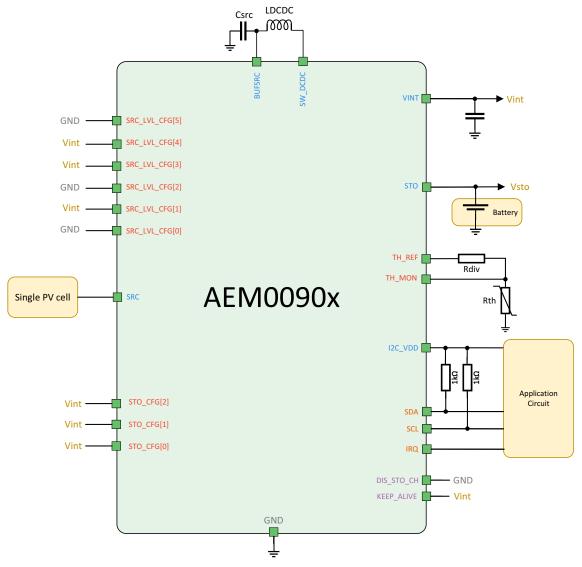


Figure 13: Typical application circuit 2

The circuit is a example of a system with solar energy harvesting with the AEM0090x. It uses a NiCd 3 cells battery as storage element.

- Energy source: PV cell
- SRC\_LVL\_CFG[5:0]: Configured through the I<sup>2</sup>C communication (0.555 V)
- STO\_CFG[2:0]: Configured through the I<sup>2</sup>C communication
  - V<sub>OVCH</sub> = 4.12 V
  - V<sub>OVDIS</sub> = 3.30 V
- The thermal monitoring is used and the thresholds are configured through the I<sup>2</sup>C communication (Cold threshold = 10°C, Hot threshold = 60°C with  $R_{DIV}$  = 22 k $\Omega$  and  $R_{TH}$ : NCP15XH103J03RC).

- DIS\_STO\_CH is connected to GND: The charging of the storage element on STO is enabled.

Register Address	Register Name	Value
0x01	SRCREGU	0011 0110
0x02	VOVDIS	0011 0010
0x03	VOVCH	0011 0011
0x04	TEMPCOLD	0111 0100
0x05	TEMPHOT	0001 1111

Table 24: Typical application circuit 2 register settings

NOTE: a configuration tool is available on e-peas website. It helps the user to read and write registers.



## 11. Circuit Behavior

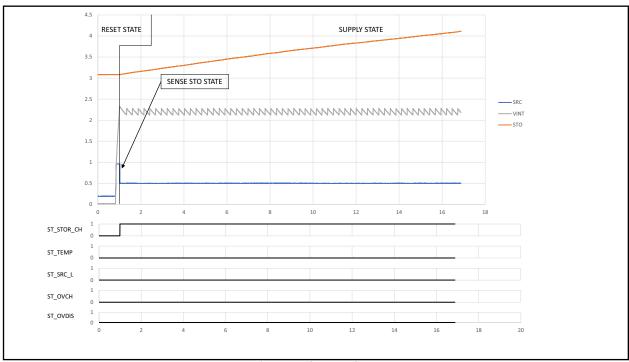


Figure 14: Start-up State

STO\_CFG[2:0] = HHH, SRC\_LVL\_CFG[5:0] = LHHLLH, storage element: capacitor (10 mF) pre-charged to 3V, SRC: current source 5 mA with voltage compliance (1.0 V), DIS\_STO\_CH = GND, KEEP\_ALIVE = H.

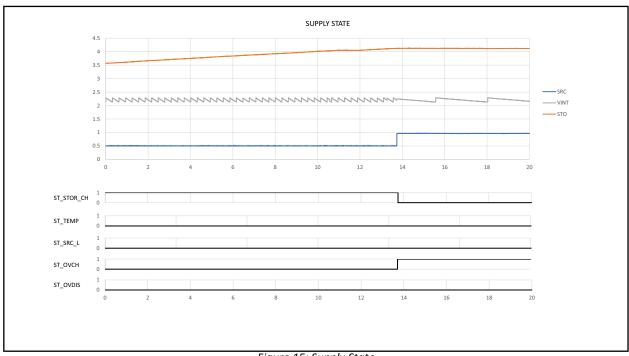


Figure 15: Supply State

STO\_CFG[2:0] = HHH, SRC\_LVL\_CFG[5:0] = LHHLLH, storage element: capacitor (10 mF) pre-charged to 3 V, SRC: current source 5 mA with voltage compliance (0.8 V), DIS\_STO\_CH = GND, KEEP\_ALIVE = H.

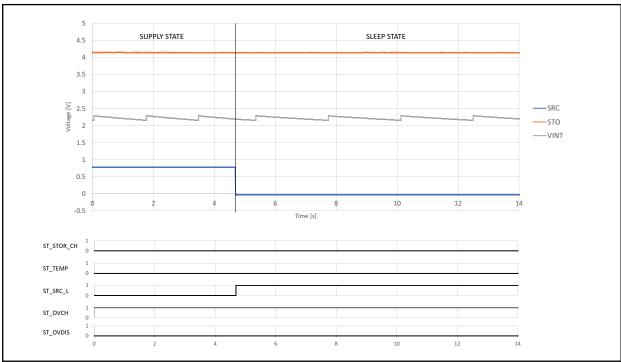


Figure 16: Behavior with the keep-alive mode and without the source

STO\_CFG[2:0] = HHH, SRC\_LVL\_CFG[5:0] = LHHLLH, storage element: capacitor (10 mF) pre-charged to 3 V, SRC: current source 5 mA with voltage compliance (0.8 V)(stop after ~4.5 sec), DIS\_STO\_CH = GND, KEEP\_ALIVE = H.

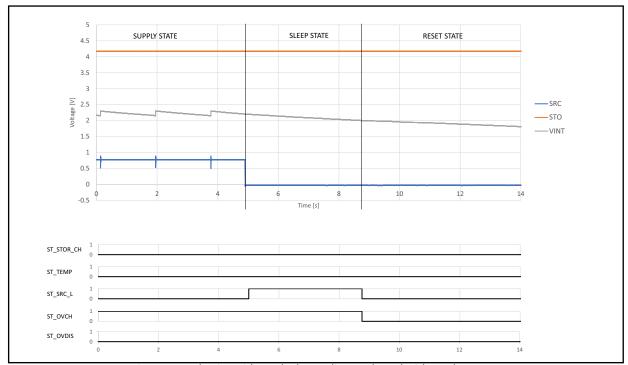


Figure 17: Behavior without the keep-alive mode and without the source

STO\_CFG[2:0] = HHH, SRC\_LVL\_CFG[5:0] = LHHLLH, storage element: capacitor (10 mF) pre-charged to 3 V, SRC: current source 5 mA with voltage compliance (0.8 V)(stop after ~5 sec), DIS\_STO\_CH = GND, KEEP\_ALIVE = L.



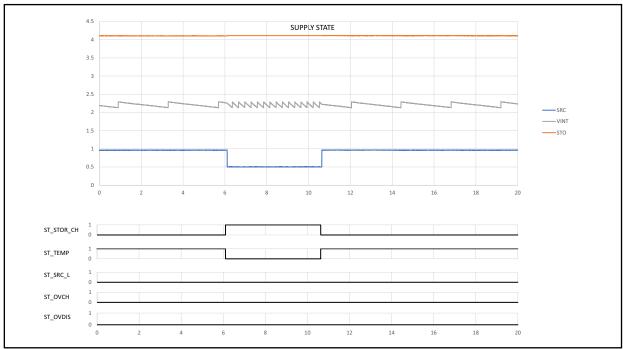


Figure 18: Thermal Monitoring Behavior

STO\_CFG[2:0] = HHH, SRC\_LVL\_CFG[5:0] = LHHLLH, storage element: capacitor (10 mF) pre-charged to 3 V, SRC: current source 5 mA with voltage compliance (0.8 V)(stop after ~5 sec), DIS\_STO\_CH = GND, KEEP\_ALIVE = H. The temperature is lower than 0 °C before 6.5 s and after 13.2 s.



# 12. Package Information

## 12.1. Plastic Quad Flatpack No-lead (QFN28 4x4mm)

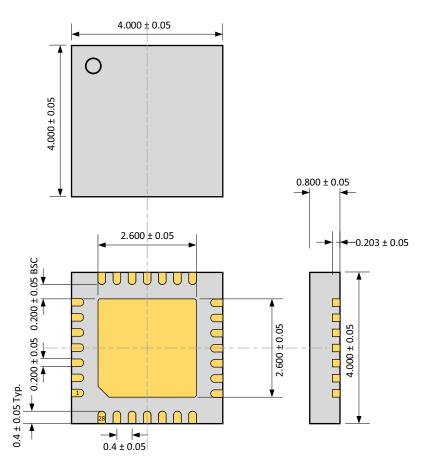


Figure 19: QFN28 4x4 mm

## 12.2. QFN28 Board Layout

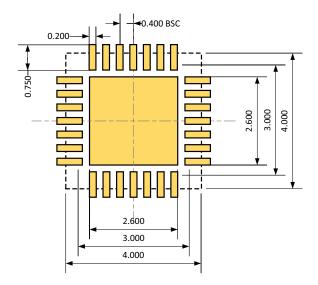


Figure 20: QFN28 4x4 mm board layout





### 12.3. Thermal Information

Package	θJΑ	θЈС	Unit
QFN28	TBD	TBD	°C/W

Table 25: Thermal information

### 12.4. Material

### 12.4.1. RoHS Compliance

e-peas product complies with RoHS requirement.

e-peas defines "RoHS" to mean that semiconductor endproducts are compliant with RoHS regulation for all 10 RoHS substances.

This applies to silicon, die attached adhesive, gold wire bonding, lead frames, mold compound, and lead finish (pure tin).

## 12.4.2. REACH Compliance

The component and elements used by e-peas subcontractors to manufacture e-peas PMICs and devices are REACH compliant. For more detailed information, please contact e-peas sales team.



## 13. Minimum BOM

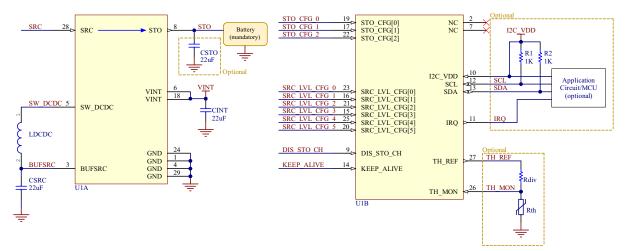


Figure 21: AEM0090x schematic

	Designator	Description	Quantity	Manufacturer	Part number
	U1	AEM0090x	1	e-peas	order at sales@e-peas.com
	Battery	Battery with 2.8 V min. voltage	1	To be defined by	the user
ory	LDCDC (AEM00900)	Power inductor 6.8 µH 1.15A 1008	1	TDK	VLS252012HBX-6R8M-1
Mandatory	LDCDC (AEM00901)	Power inductor 33 μH 680 mA 1515	1	Coilcraft	LPS4018-333MRB
Mar	CSRC	Ceramic capacitor 22 μF 6.3 V 20% X5R 0402	1	Murata	GRM158R60J226ME01
	CINT	Ceramic capacitor 22 μF 6.3 V 20% X5R 0402	1	Murata	GRM158R60J226ME01
	CSTO	Ceramic capacitor 22 μF 6.3 V 20% X5R 0402	1	Murata	GRM158R60J226ME01
al	R1, R2	Pull-up 1 kΩ Resistors for I <sup>2</sup> C interface	2	Yageo	AC0603FR-071KL
Optional	Rth	10 k $\Omega$ NTC thermistor for temperature monitoring	1	Murata	NCP15XH103J03RC
Ор	Rdiv	Resistor 22 kΩ 1%	1	Yageo	PNRC0402FR-0722KL

Table 26: AEM0090x bill of material





## 14. Layout

The following Figures are showcasing layout examples of the AEM0090x.

The following guidelines must be applied for best performances:

- Make sure that ground and power signals are routed with large tracks. If an internal ground plane is used, place via as close as possible to the components, especially for decoupling capacitors.
- Reactive components related to the boost converter must be placed as close as possible to the corresponding pins (SWDCDC, BUFSRC and STO), and be routed with large tracks/polygons.

- PCB track capacitance must be reduced as much as possible on the boost converter switching node SWDCDC. This is done as follows:
  - Keep the connection between the SWDCDC pin and the inductor short.
  - Remove the ground and power planes under the SWDCDC node. The polygon on the opposite external layer may also be removed.
  - Increase the distance between SWDCDC and the ground polygon on the external PCB layer where the AEM0090x is mounted.
- PCB track capacitance must be reduced as much as possible on the TH\_REF node. Same principle as for SWDCDC may be applied.

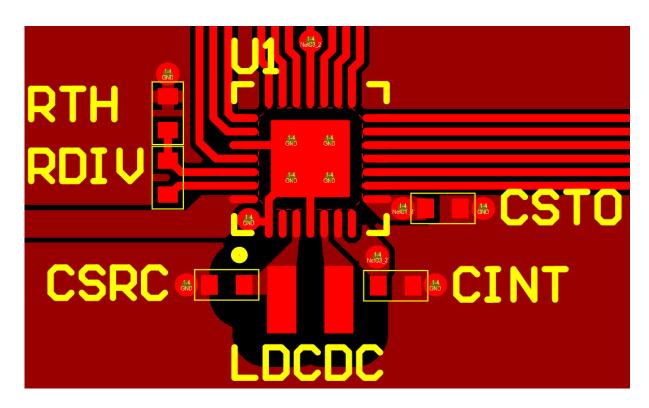


Figure 22: AEM00900 QFN28 layout example



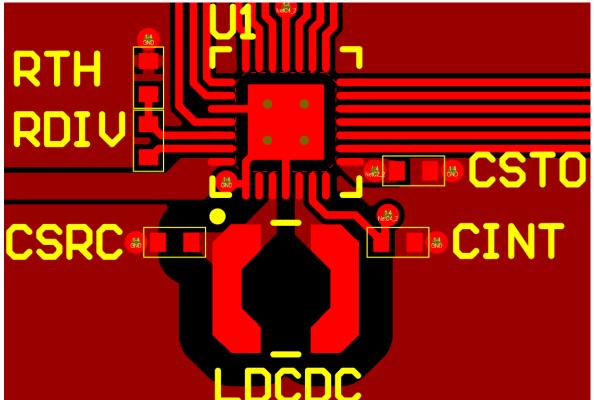


Figure 23: AEM00901 QFN28 layout example





## 15. Glossary

### $V_{\text{STO}}$

Voltage at STO pin.

### V<sub>SRC,REG</sub>

Target regulation voltage at the SRC pin.

#### V<sub>SRC.CS</sub>

Minimum source voltage required for cold start.

### $V_{SRC}$

Voltage at SRC pin.

#### Vovois

Overdischarge voltage at STO pin.

## $\mathbf{V}_{\text{OVCH}}$

Overcharge voltage at STO pin.

#### Voc

Open-circuit voltage of the harvester connected to the SRC pin.

### **VINT**

AEM0090x internal circuit voltage supply.

### V<sub>INT,CS</sub>

Minimum voltage on VINT to allow the AEM0090x to switch from RESET STATE to SENSE STO STATE.

### P<sub>SRC,CS</sub>

Minimum power available on SRC for the AEM0090x to coldstart.

### IQSUPPLY

Quiescent current on VINT when the AEM0090x is in SUPPLY STATE.

#### IOSLEEP

Quiescent current on VINT when the AEM0090x is in SLEEP STATE.

#### IOSTO

Quiescent current on STO when Keep-alive functionality is disabled.

### I<sub>QSTO</sub>

Quiescent current on STO when Keep-alive functionality is disabled.

### I<sub>SRC</sub>

Current drawn at the SRC pin.

### **R**<sub>DIV</sub>

Resistor that creates a resistive voltage divider with R<sub>TH</sub>.

### CINT

VINT pin decoupling capacitor.

### CSRC

**BUFSRC** pin decoupling capacitor.

### L<sub>DCDC</sub>

DCDC converter inductor.

### R<sub>SCL</sub> / R<sub>SDA</sub>

Respectively, I<sup>2</sup>C SCL and SDA pin pull-up resistors.





# **16. Revision History**

Revision	Date	Description
1.0	January, 2022	Creation of the document.
1.1	February, 2023	<ul> <li>I2C_VDD: max. voltage to 2.2 V.</li> <li>I2C_VDD: more explanation about pin use when using I²C and not using I²C.</li> <li>Added component part number.</li> <li>LDCDC from 4.7 μH to 6.8 μH in typical application circuits and in efficiency graphs (AEM00900).</li> <li>Explanations about CSTO influence on efficiency.</li> </ul>
1.2	February, 2024	- Thermal pad (back plane) renamed as pin 29.
1.3	August, 2024	<ul> <li>Small fixes.</li> <li>Modified V<sub>SRC,REG</sub> register format.</li> <li>Removed register 0x13.</li> </ul>
1.4	September, 2024	- Corrected typos and improved some sentences structure.

Table 27: Revision history